

# SN74HCS05-Q1 Automotive Hex Inverter with Open-Drain Outputs and Schmitt-Trigger Inputs

## 1 Features

- AEC-Q100 Qualified for automotive applications:
  - Device temperature grade 1:  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ ,  $T_A$
  - Device HBM ESD Classification Level 2
  - Device CDM ESD Classification Level C6
- Wide operating voltage range: 2 V to 6 V
- Schmitt-trigger inputs allow for slow or noisy input signals
- Low power consumption
  - Typical  $I_{CC}$  of 100 nA
  - Typical input leakage current of  $\pm 100$  nA
- $\pm 7.8$ -mA output drive at 5 V

## 2 Applications

- Drive indicator LEDs
- Level-shift using open-drain outputs
- Invert a digital signal

## 3 Description

This device contains six independent inverter with open-drain outputs and Schmitt-trigger inputs. Each gate performs the Boolean function  $Y = \bar{A}$  in positive logic.

**Device Information<sup>(1)</sup>**

| PART NUMBER     | PACKAGE    | BODY SIZE (NOM)   |
|-----------------|------------|-------------------|
| SN74HCS05QPWRQ1 | TSSOP (14) | 5.00 mm x 4.40 mm |
| SN74HCS05QDRQ1  | SOIC (14)  | 8.70 mm x 3.90 mm |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

### Benefits of Schmitt-trigger Inputs

|   | Low Power | Noise Rejection | Supports Slow Inputs |
|---|-----------|-----------------|----------------------|
| Input Voltage Waveforms                       |           |                 |                      |
| Standard CMOS Input Response Waveforms        |           |                 |                      |
| Schmitt-trigger CMOS Input Response Waveforms |           |                 |                      |



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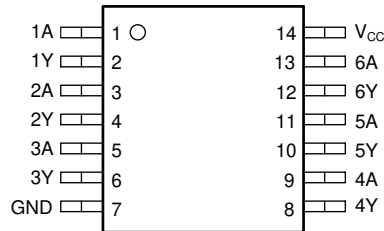
## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

| DATE      | REVISION | NOTES            |
|-----------|----------|------------------|
| June 2020 | *        | Initial release. |

## 5 Pin Configuration and Functions

PW or D Package  
14-Pin TSSOP or SOIC  
Top View



Pin Functions

| PIN             |     | I/O    | DESCRIPTION         |
|-----------------|-----|--------|---------------------|
| NAME            | NO. |        |                     |
| 1A              | 1   | Input  | Channel 1, Input A  |
| 1Y              | 2   | Output | Channel 1, Output Y |
| 2A              | 3   | Input  | Channel 2, Input A  |
| 2Y              | 4   | Output | Channel 2, Output Y |
| 3A              | 5   | Input  | Channel 3, Input A  |
| 3Y              | 6   | Output | Channel 3, Output Y |
| GND             | 7   | —      | Ground              |
| 4Y              | 8   | Output | Channel 4, Output Y |
| 4A              | 9   | Input  | Channel 4, Input A  |
| 5Y              | 10  | Output | Channel 5, Output Y |
| 5A              | 11  | Input  | Channel 5, Input A  |
| 6Y              | 12  | Output | Channel 6, Output Y |
| 6A              | 13  | Input  | Channel 6, Input A  |
| V <sub>CC</sub> | 14  | —      | Positive Supply     |

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

|                  |   | MIN  | MAX | UNIT |
|------------------|---|--|-----|------|
| V <sub>CC</sub>  | Supply voltage                                    | −0.5   | 7   | V    |
| I <sub>IK</sub>  | Input clamp current <sup>(2)</sup>                | V <sub>I</sub> < 0 or V <sub>I</sub> > V <sub>CC</sub> + 0.5 | ±20 | mA   |
| I <sub>OK</sub>  | Output clamp current <sup>(2)</sup>               | V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub> + 0.5 | ±20 | mA   |
| I <sub>O</sub>   | Continuous output current                         | V <sub>O</sub> = 0 to V <sub>CC</sub>                        | ±35 | mA   |
|                  | Continuous current through V <sub>CC</sub> or GND |  | ±70 | mA   |
| T <sub>J</sub>   | Junction temperature <sup>(3)</sup>               |  | 150 | °C   |
| T <sub>stg</sub> | Storage temperature                               | −65  | 150 | °C   |

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

(3) Guaranteed by design.

## 6.2 ESD Ratings

|                    |                         |   | VALUE | UNIT |
|--------------------|-------------------------|---|-------|------|
| V <sub>(ESD)</sub> | Electrostatic discharge | Human body model (HBM), per AEC Q100-002 <sup>(1)</sup><br>HBM ESD Classification Level 2 | ±4000 | V    |
|                    |                         | Charged device model (CDM), per AEC Q100-011<br>CDM ESD Classification Level C6           | ±1500 |      |

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

|                 |                     | MIN | NOM | MAX             | UNIT |
|-----------------|---------------------|-----|-----|-----------------|------|
| V <sub>CC</sub> | Supply voltage      | 2   | 5   | 6               | V    |
| V <sub>I</sub>  | Input voltage       | 0   |     | V <sub>CC</sub> | V    |
| V <sub>O</sub>  | Output voltage      | 0   |     | V <sub>CC</sub> | V    |
| T <sub>A</sub>  | Ambient temperature | –40 |     | 125             | °C   |

## 6.4 Thermal Information

| THERMAL METRIC        |  | SN74HCS05-Q1 |          | UNIT |
|-----------------------|--|--------------|----------|------|
|                       |  | PW (TSSOP)   | D (SOIC) |      |
|                       |  | 14 PINS      | 14 PINS  |      |
| R <sub>θJA</sub>      | Junction-to-ambient thermal resistance       | 151.7        | 133.6    | °C/W |
| R <sub>θJC(top)</sub> | Junction-to-case (top) thermal resistance    | 79.4         | 89.0     | °C/W |
| R <sub>θJB</sub>      | Junction-to-board thermal resistance         | 94.7         | 89.5     | °C/W |
| Ψ <sub>JT</sub>       | Junction-to-top characterization parameter   | 25.2         | 45.5     | °C/W |
| Ψ <sub>JB</sub>       | Junction-to-board characterization parameter | 94.1         | 89.1     | °C/W |
| R <sub>θJC(bot)</sub> | Junction-to-case (bottom) thermal resistance | N/A          | N/A      | °C/W |

## 6.5 Electrical Characteristics

over operating free-air temperature range; typical values measured at T<sub>A</sub> = 25°C (unless otherwise noted).

| PARAMETER       |   | TEST CONDITIONS   | V <sub>CC</sub>          | MIN        | TYP   | MAX   | UNIT |      |
|-----------------|---|---|--------------------------|------------|-------|-------|------|------|
| V <sub>T+</sub> | Positive switching threshold                    |   | 2 V                      | 0.7        |       | 1.5   | V    |      |
|                 |   |   | 4.5 V                    | 1.7        |       | 3.15  |      |      |
|                 |   |   | 6 V                      | 2.1        |       | 4.2   |      |      |
| V <sub>T-</sub> | Negative switching threshold                    |   | 2 V                      | 0.3        |       | 1.0   | V    |      |
|                 |   |   | 4.5 V                    | 0.9        |       | 2.2   |      |      |
|                 |   |   | 6 V                      | 1.2        |       | 3.0   |      |      |
| ΔV <sub>T</sub> | Hysteresis (V <sub>T+</sub> - V <sub>T-</sub> ) |   | 2 V                      | 0.2        |       | 1.0   | V    |      |
|                 |   |   | 4.5 V                    | 0.4        |       | 1.4   |      |      |
|                 |   |   | 6 V                      | 0.6        |       | 1.6   |      |      |
| V <sub>OL</sub> | Low-level output voltage                        | V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>       | I <sub>OL</sub> = 20 μA  | 2 V to 6 V | 0.002 | 0.1   | V    |      |
|                 |   |   | I <sub>OL</sub> = 6 mA   | 4.5 V      |       | 0.18  |      | 0.30 |
|                 |   |   | I <sub>OL</sub> = 7.8 mA | 6 V        |       | 0.22  |      | 0.33 |
| I <sub>I</sub>  | Input leakage current                           | V <sub>I</sub> = V <sub>CC</sub> or 0                     | 6 V                      |            | ±100  | ±1000 | nA   |      |
| I <sub>CC</sub> | Supply current                                  | V <sub>I</sub> = V <sub>CC</sub> or 0, I <sub>O</sub> = 0 | 6 V                      |            | 0.1   | 2     | μA   |      |
| C <sub>i</sub>  | Input capacitance                               |   | 2 V to 6 V               |            |       | 5     | pF   |      |
| C <sub>PD</sub> | Power dissipation capacitance per gate          | No load   | 2V to 6 V                |            | 10    |       | pF   |      |

## 6.6 Switching Characteristics

over operating free-air temperature range; typical values measured at  $T_A = 25^\circ\text{C}$  (unless otherwise noted). See [Parameter Measurement Information](#).

| PARAMETER |                   | FROM (INPUT) | TO (OUTPUT) | $V_{CC}$ | MIN | TYP | MAX | UNIT |
|-----------|-------------------|--------------|-------------|----------|-----|-----|-----|------|
| $t_{pd}$  | Propagation delay | A            | Y           | 2 V      |     | 18  | 39  | ns   |
|           |                   |              |             | 4.5 V    |     | 13  | 15  |      |
|           |                   |              |             | 6 V      |     | 12  | 15  |      |
| $t_t$     | Transition-time   |              | Y           | 2 V      |     | 9   | 16  | ns   |
|           |                   |              |             | 4.5 V    |     | 5   | 9   |      |
|           |                   |              |             | 6 V      |     | 4   | 8   |      |

## 6.7 Typical Characteristics

$T_A = 25^\circ\text{C}$

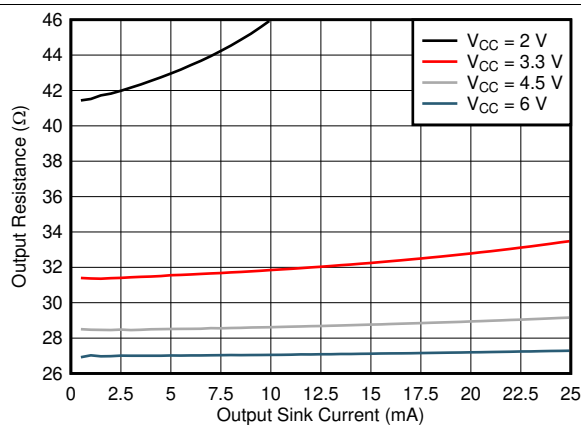


Figure 1. Output driver resistance in Low state

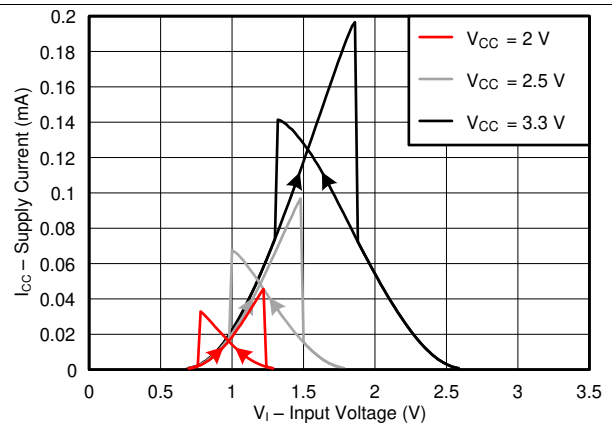


Figure 2. Typical supply current versus input voltage across common supply values (2 V to 3.3 V)

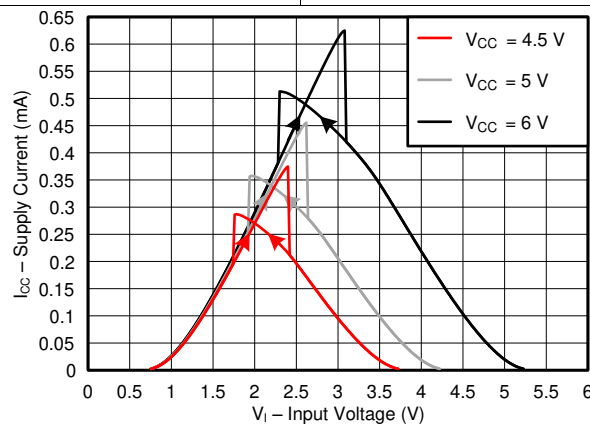
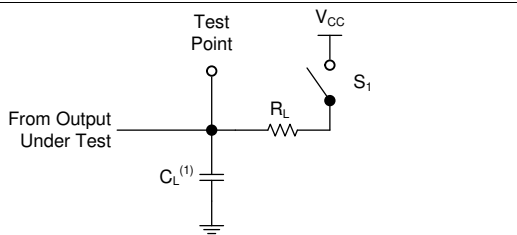


Figure 3. Typical supply current versus input voltage across common supply values (4.5 V to 6 V)

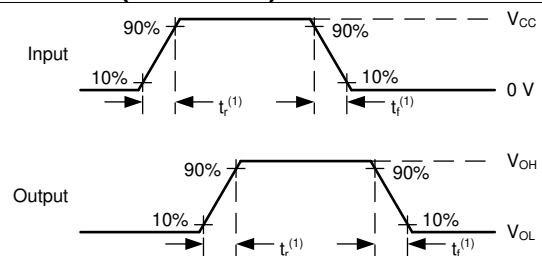
## 7 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 1 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_t < 6 \text{ ns}$ .
- The outputs are measured one at a time, with one input transition per measurement.

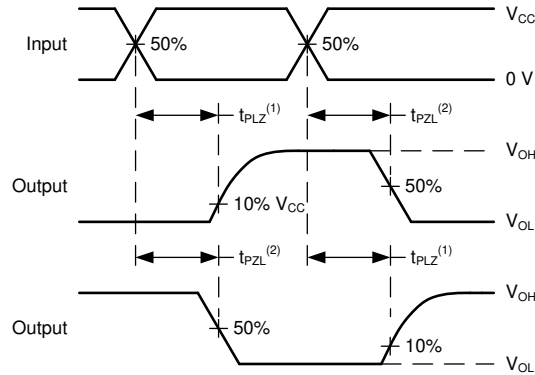
**Parameter Measurement Information (continued)**



$C_L = 50$  pF and includes probe and jig capacitance.  
**Figure 4. Load Circuit**



**Figure 5. Voltage Waveforms Transition Times**



The maximum between  $t_{PLH}$  and  $t_{PHL}$  is used for  $t_{pd}$ .

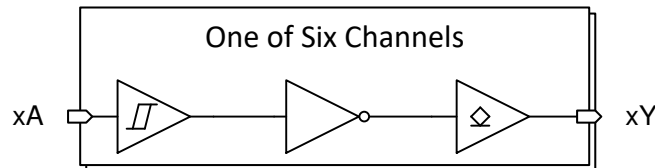
**Figure 6. Voltage Waveforms Propagation Delays**

## 8 Detailed Description

### 8.1 Overview

This device contains six independent inverter with open-drain outputs and Schmitt-trigger inputs. Each gate performs the Boolean function  $Y = \bar{A}$  in positive logic.

### 8.2 Functional Block Diagram



### 8.3 Feature Description

#### 8.3.1 CMOS Open-Drain Outputs

The open-drain output allows the device to sink current to GND but not to source current from  $V_{CC}$ . When the output is not actively pulling the line low, it will go into a high impedance state. This allows the device to be used for a wide variety of applications, including up-translation and down-translation, as the output voltage can be determined by an external pull-up resistor.

The current drive capability of this device creates fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined in the [Absolute Maximum Ratings](#) must be followed at all times.

The SN74HCS05-Q1 can drive a load with a total capacitance less than or equal to the maximum load listed in the connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed the provided load value. If larger capacitive loads are required, it is recommended to add a series resistor between the output and the capacitor to limit output current to the values given in the [Absolute Maximum Ratings](#).

#### 8.3.2 CMOS Schmitt-Trigger Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor from the input to ground in parallel with the input capacitance given in the [Electrical Characteristics](#). The worst case resistance is calculated with the maximum input voltage, given in the [Absolute Maximum Ratings](#), and the maximum input leakage current, given in the [Electrical Characteristics](#), using ohm's law ( $R = V \div I$ ).

The Schmitt-trigger input architecture provides hysteresis as defined by  $\Delta V_T$  in the [Electrical Characteristics](#), which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs slowly will also increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see [Understanding Schmitt Triggers](#).

## Feature Description (continued)

### 8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in [Figure 7](#).

**CAUTION**

Voltages beyond the values specified in the [Absolute Maximum Ratings](#) table can cause damage to the device. The recommended input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



**Figure 7. Electrical Placement of Clamping Diodes for Each Input and Output**

## 8.4 Device Functional Modes

**Table 1. Function Table**

| INPUT | OUTPUT |
|-------|--------|
| A     | Y      |
| L     | Z      |
| H     | L      |



## 9 Application and Implementation

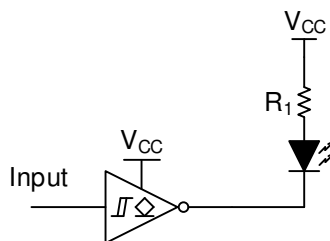
### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

In this application, the device is used to drive an indicator LED directly. Unused channels should have the inputs terminated at either  $V_{CC}$  or GND, whichever is more convenient, and the outputs should be left disconnected.

### 9.2 Typical Application



**Figure 8. Typical application block diagram**

#### 9.2.1 Design Requirements

##### 9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the [Recommended Operating Conditions](#). The supply voltage sets the device's electrical characteristics as described in the [Electrical Characteristics](#).

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS05-Q1 plus the maximum supply current,  $I_{CC}$ , listed in [Electrical Characteristics](#). The logic device can only sink as much current as is provided by the external pull-up resistor or other supply source. Be sure not to exceed the maximum total current through GND listed in the [Absolute Maximum Ratings](#).

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and  \$C\_{pd}\$  Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

### CAUTION

The maximum junction temperature,  $T_J(\text{max})$  listed in the [Absolute Maximum Ratings](#), is an *additional limitation* to prevent damage to the device. Do not violate any values listed in the [Absolute Maximum Ratings](#). These limits are provided to prevent damage to the device.

##### 9.2.1.2 Input Considerations

Input signals must cross  $V_{t(\text{min})}$  to be considered a logic LOW, and  $V_{t(\text{max})}$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the [Absolute Maximum Ratings](#).

## Typical Application (continued)

Unused inputs must be terminated to either  $V_{CC}$  or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCS05-Q1, as specified in the [Electrical Characteristics](#), and the desired input transition rate. A 10-k $\Omega$  resistor value is often used due to these factors.

The SN74HCS05-Q1 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the  $\Delta V_T(\text{min})$  in the [Electrical Characteristics](#). This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than  $V_{CC}$  or ground is plotted in the [Typical Characteristics](#).

Refer to the [Feature Description](#) for additional information regarding the inputs for this device.

### 9.2.1.3 Output Considerations

The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the [Electrical Characteristics](#). The plot in provides a typical relationship between output voltage and current for this device.

Open-drain outputs can be directly connected together to produce a wired-AND. This is possible because the outputs cannot source current, and thus can never be in bus-contention.

Unused outputs can be left floating. Do not connect outputs directly to  $V_{CC}$  or ground.

Refer to [Feature Description](#) for additional information regarding the outputs for this device.

### 9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from  $V_{CC}$  to GND. The capacitor needs to be placed physically close to the device and electrically close to both the  $V_{CC}$  and GND pins. An example layout is shown in the [Layout](#).
2. Ensure the capacitive load at the output is  $\leq 70$  pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS05-Q1 to the receiving device.
3. Ensure the resistive load at the output is larger than  $(V_{CC} / I_{O(\text{max})}) \Omega$ . This will ensure that the maximum output current from the [Absolute Maximum Ratings](#) is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#)

### 9.2.3 Application Curves

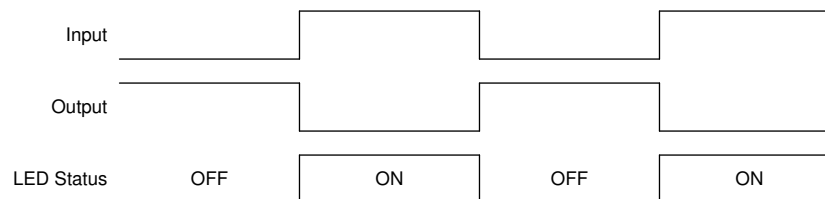


Figure 9. Application timing diagram

## 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the [Recommended Operating Conditions](#). Each  $V_{CC}$  terminal should have a bypass capacitor to prevent power disturbance. A 0.1- $\mu\text{F}$  capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu\text{F}$  and 1- $\mu\text{F}$  capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in [Figure 10](#).

## 11 Layout

### 11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.

### 11.2 Layout Example

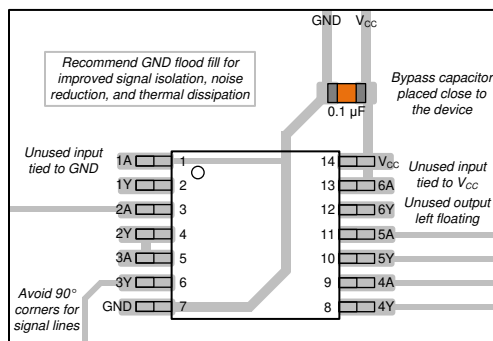


Figure 10. Example layout for the SN74HCS05-Q1

## 12 Device and Documentation Support

### 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation see the following:

- [Reduce Noise and Save Power with the New HCS Logic Family](#)
- [CMOS Power Consumption and CPD Calculation](#)
- [Designing with Logic](#)

### 12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

### 12.3 Community Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

### 12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

### 12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

| Orderable Device | Status<br>(1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan<br>(2)         | Lead finish/<br>Ball material<br>(6) | MSL Peak Temp<br>(3) | Op Temp (°C) | Device Marking<br>(4/5) | Samples |
|------------------|---------------|--------------|-----------------|------|-------------|-------------------------|--------------------------------------|----------------------|--------------|-------------------------|---------|
| SN74HCS05QDRQ1   | PREVIEW       | SOIC         | D               | 14   | 2500        | Green (RoHS & no Sb/Br) | NIPDAU                               | Level-1-260C-UNLIM   | -40 to 125   | HCS05Q1                 |         |
| SN74HCS05QPWRQ1  | PREVIEW       | TSSOP        | PW              | 14   | 2000        | Green (RoHS & no Sb/Br) | NIPDAU                               | Level-1-260C-UNLIM   | -40 to 125   | HCS05Q                  |         |

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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